

## SANYO Semiconductors

### DATA SHEET

N-Channel Silicon MOSFET

# MCH6431 — General-Purpose Switching Device Applications

#### **Features**

- ON-resistance RDS(on)1= $42m\Omega$  (typ.)
- · 4V drive
- · Halogen free compliance.

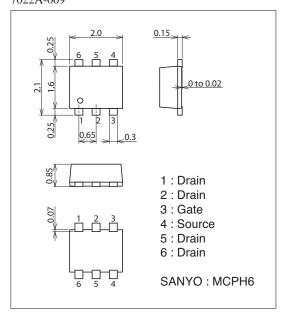
#### **Specifications**

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	20	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm <sup>2</sup> x0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7022A-009

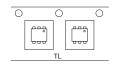


#### **Product & Package Information**

• Package : MCPH6

JEITA, JEDEC : SC-88, SOT-363
Minimum Packing Quantity : 3,000 pcs./reel

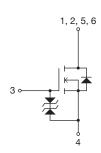
#### Packing Type: TL



#### Marking



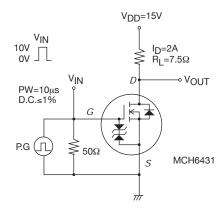
#### **Electrical Connection**

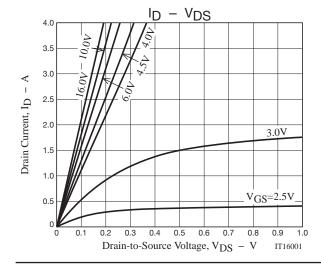


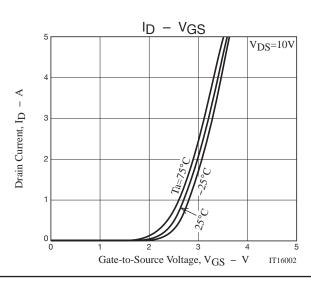
#### Electrical Characteristics at Ta=25°C

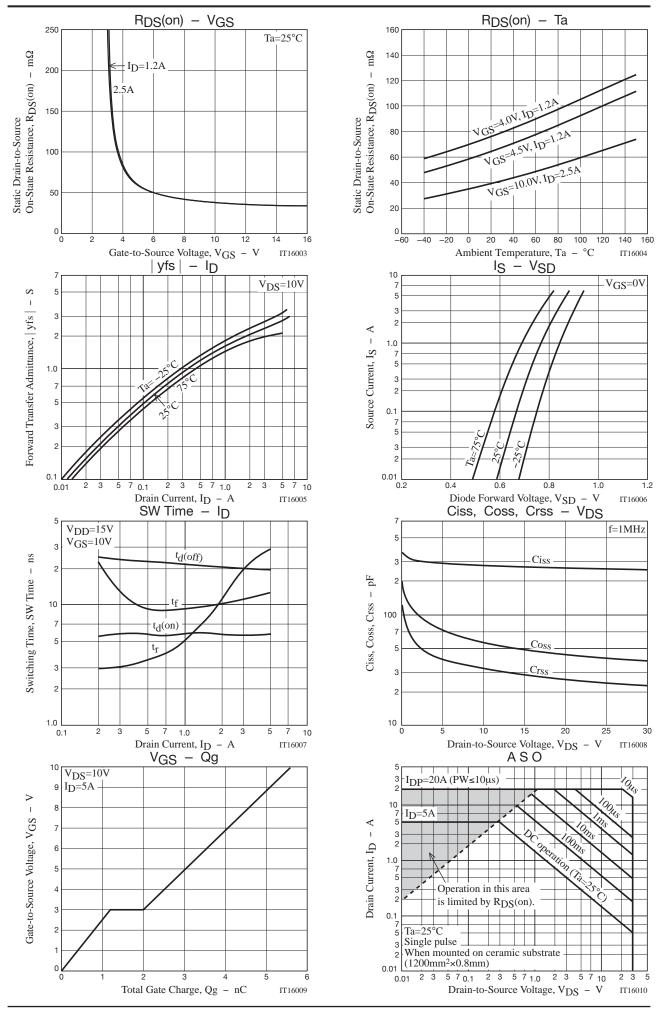
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =2.5A		2.2		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =2.5A, V <sub>GS</sub> =10V		42	55	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.2A, V <sub>GS</sub> =4.5V		65	91	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1.2A, V <sub>GS</sub> =4V		78	109	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		280		рF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		60		рF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		30		рF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		5.7		ns
Rise Time	tr	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		21		ns
Fall Time	tf	See specified Test Circuit.		10		ns
Total Gate Charge	Qg	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		5.6		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		1.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		0.8		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =5A, V <sub>GS</sub> =0V		0.85	1.2	V

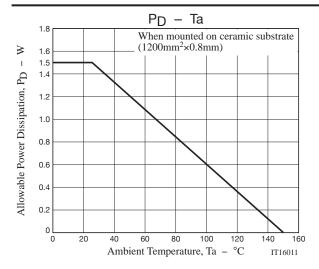
#### **Switching Time Test Circuit**











Note on usage: Since the MCH6431 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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